

1                   ABSTRACT OF THE DISCLOSURE

2                   The invention includes a method of forming a capacitor structure.  
3                   A first electrical node is formed, and a layer of metallic aluminum is  
4                   formed over the first electrical node. Subsequently, an entirety of the  
5                   metallic aluminum within the layer is transformed into one or more of  
6                   AlN, AlON, and AlO, with the transformed layer being a dielectric  
7                   material over the first electrical node. A second electrical node is then  
8                   formed over the dielectric material. The first electrical node, second  
9                   electrical node and dielectric material together define at least a portion  
10                  of the capacitor structure. The invention also pertains to a capacitor  
11                  structure which includes a first electrical node, a second electrical node,  
12                  and a dielectric material between the first and second electrical nodes.  
13                  The dielectric material consists essentially of aluminum, oxygen and  
14                  nitrogen.